What is claimed is:

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A computer system comprising:

- a memory controller;
- a main memory bus coupled to the memory controller; and
- a synchronous non-volatile memory device coupled to the main memory bus.
- 2. The computer system of claim 1 wherein the synchronous non-volatile memory device has a command interface comprising:
 - a write enable connection (WE#) to receive a write enable signal;
- a column address strobe connection (CAS#) to receive a column address strobe

signal;

a row address strobe connection (RAS#) to receive a row address strobe signal;

and

a chip select connection (CS#) to receive a chip select signal.

3. A synchronous flash memory device comprising:

an array of non-volatile memory cells; and

- a plurality of external connections comprising,
- a plurality of bi-directional data connections,
- a plurality of memory address connections,
- a clock input/connection,
- a write enable connection,
- a column address strobe connection, and
- a row address strobe connection.
- 4. The synchronous flash memory device of claim 3 wherein the plurality of external connections further comprises:

a clock enable connection,

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a chip select connection,
a plurality of memory array bank address connections,
power supply connections,
a plurality of data mask connections, and
a reset connection.

- 5. The synchronous flash memory device of claim 3 wherein the plurality of external connections further comprises a Vccp power supply connection.
- 6. The synchronous flash memory device of claim 3 further comprising a package having a plurality of interconnect pins corresponding to the external connections.
- 7. The synchronous flash memory device of claim 6 wherein the interconnect pins are physically arranged in a pattern compatible with a synchronous dynamic random access memory (SDRAM).
- 8. The synchronous flash memory device of claim 3 further comprising a package having a plurality of conductive interconnect locations corresponding to the external connections.
- 9. The synchronous flash memory device of claim 8 wherein the conductive interconnect locations are physically arranged in a pattern compatible with a synchronous dynamic random access memory (SDRAM).
- 10. The synchronous flash memory device of claim 9 further wherein the synchronous flash memory device operates within read timing specification parameters for an SDRAM.

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11. A synchronous flash memory device comprising:

an array of non-volatile memory cells; and

a package having a plurality of interconnect pins arranged in a manner that corresponds to interconnect pins of a synchronous dynamic random access memory device, wherein the plurality of interconnect pins of the synchronous flash memory device comprises a reset connection, and a Vccp power supply connection correspond to first and second no-connect (NC) interconnect pins of the synchronous dynamic random access memory.

12. The synchronous flash memory device of claim 11 wherein the plurality of interconnect pins comprises:

a plurality of bi-directional data connections,

a plurality of memory address connections,

a write enable connection,

a clock input connection,

a column address strobe connection,

a row address strobe connection, and

power supply connections.

13. The synchronous flash memory device of claim 12 wherein the plurality of interconnect pins further comprises:

a clock enable connection,

a chip select connection,

a plurality of memory array bank address connections,

a plurality of data mask connections,

a reset connection, and

a Vccp power supply connection.

14. A synchronous flash memory device comprising:

an array of non-volatile memory cells; and

a package having a plurality of solder bump connections arranged in a manner that corresponds to solder bump connections of a synchronous dynamic random access memory device, wherein the plurality of solder bump connections of the synchronous flash memory device comprises a reset connection, and a Vccp power supply connection correspond to first and second no-connect (NC) solder bump connections of the synchronous dynamic random access memory.

- 15. The synchronous flash memory device of claim 14 wherein the plurality of solder bump connections comprises:
 - a plurality of bi-directional data connections,
 - a plurality of memory address connections,
 - a write enable connection,
 - a clock input connection,
 - a column address strobe connection,
 - a row address strobe connection, and
 - power supply connections.
- 16. The synchronous flash memory device of claim 15 wherein the plurality of interconnect pins further comprises:
 - a clock enable connection,
 - a chip select connection,
 - a plurality of memory array bank address connections,
 - a plurality of data mask connections,
 - a reset connection, and
 - a Vccp power supply connection.

- 17. A synchronous flash memory device having an interface comprising:
 - a clock input connection (CLK) to receive a clock signal;
 - a write enable connection (WE#) to receive a write enable signal;
- a column address strobe connection (CAS#) to receive a column address strobe signal;
 - a row address strobe connection (RAS#) to receive a row address strobe signal;
 - a chip select connection (CS#) to receive a chip select signal;
 - a reset connection (RP#) to receive a reset signal; and
 - a Vccp power supply connection to receive an elevated power supply signal.
- 18. The synchronous flash memory device of claim 17 wherein the interface further comprises:
 - a plurality of bi-directional data connections (DQ);
 - a plurality of memory address connections;
 - a clock enable connection (CKE);
 - a plurality of memory array bank address connections (BA#);
 - power supply connections (Vcc and Vss); and
 - a plurality of data mask connections (DQM).
- 19. The synchronous flash memory device of claim 18 further comprising a package having a plurality of interconnect pins corresponding to the command interface connections.
- 20. The synchronous flash memory device of claim 19 wherein the interconnect pins are physically arranged in a pattern compatible with a synchronous dynamic random access memory (SDRAM).

- 21. The synchronous flash memory device of claim 18 further comprising a package having a plurality of conductive interconnect locations corresponding to the command interface connections.
- 22. The synchronous flash memory device of claim 21 wherein the conductive interconnect locations are physically arranged in a pattern compatible with a synchronous dynamic random access memory (SDRAM).
- 23. A computer system comprising:
 - a memory controller;
 - a main memory bus coupled to the memory controller; and
- a synchronous non-volatile flash memory device coupled to the main memory bus, wherein the synchronous non-volatile flash memory device has a command interface comprising:
 - a write enable connection (WE#) to receive a write enable signal;
- a column address strobe connection (CAS#) to receive a column address strobe signal;
- a row address strobe connection (RAS#) to receive a row address strobe signal;
 - a chip select connection (CS#) to receive a chip select signal.
- 24. The computer system of claim 23 wherein the synchronous non-volatile flash memory device comprises a package having a plurality of interconnect pins arranged in a manner that corresponds to interconnect pins of a synchronous dynamic random access memory device, wherein the plurality of interconnect pins of the synchronous flash memory device comprises a reset connection, and a Vccp power supply connection correspond to first and second no connect (NC) interconnect pins of the synchronous dynamic random access memory.

- 25. The computer system of claim 23 wherein the synchronous non-volatile flash memory device comprises a package having a plurality of solder bump connections arranged in a manner that corresponds to solder bump connections of a synchronous dynamic random access memory device, wherein the plurality of solder bump connections of the synchronous flash memory device comprises a reset connection, and a Vccp power supply connection correspond to first and second no-connect (NC) solder bump connections of the synchronous dynamic random access memory.
- 26. The computer system of claim 23 wherein the synchronous non-volatile flash memory device comprises a plurality of external connections comprising:
 - a plurality of bi-directional data connections;
 - a plurality of memory address connections;
 - a clock input connection;
 - a clock enable connection;
 - a plurality of memory array bank address connections;
 - power supply connections;
 - a plurality of data mask connections;
 - a reset connection; and
 - a Vccp power supply connection.

